

FIG. 1A

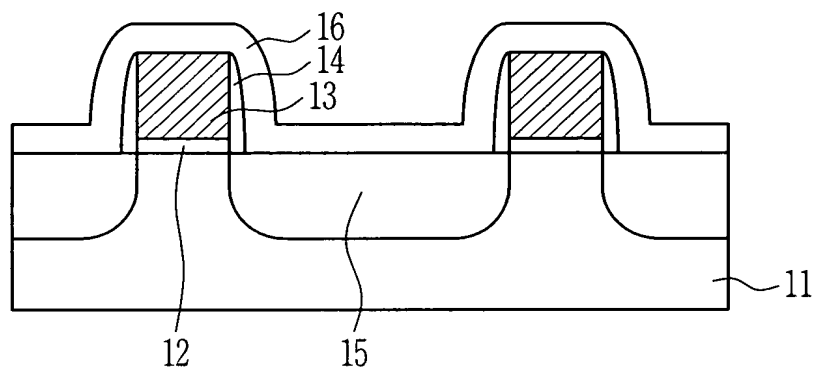


FIG. 1B

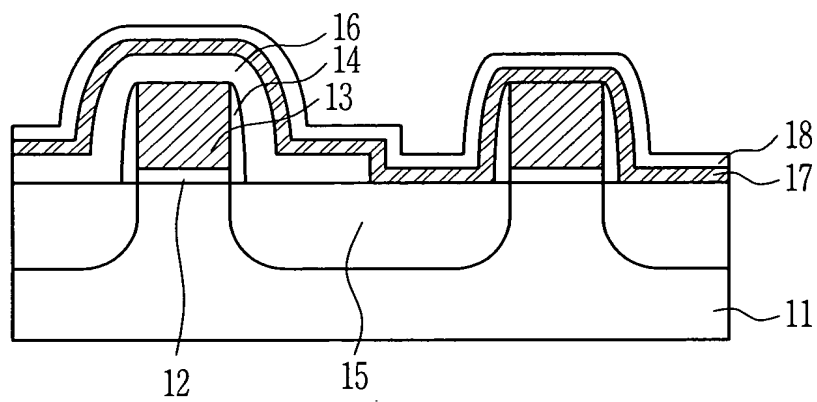
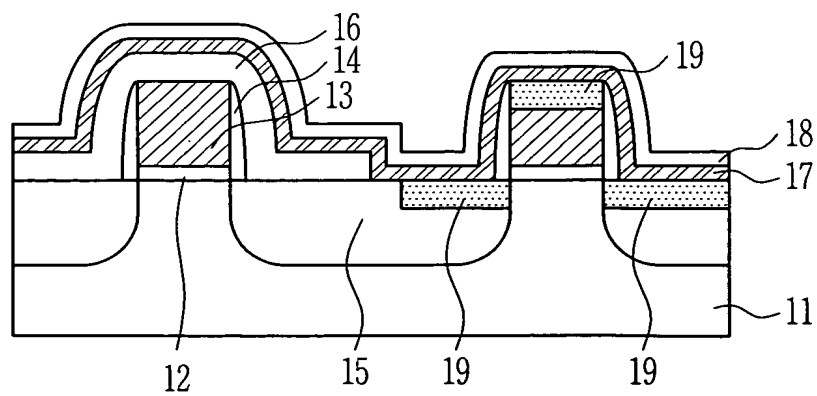
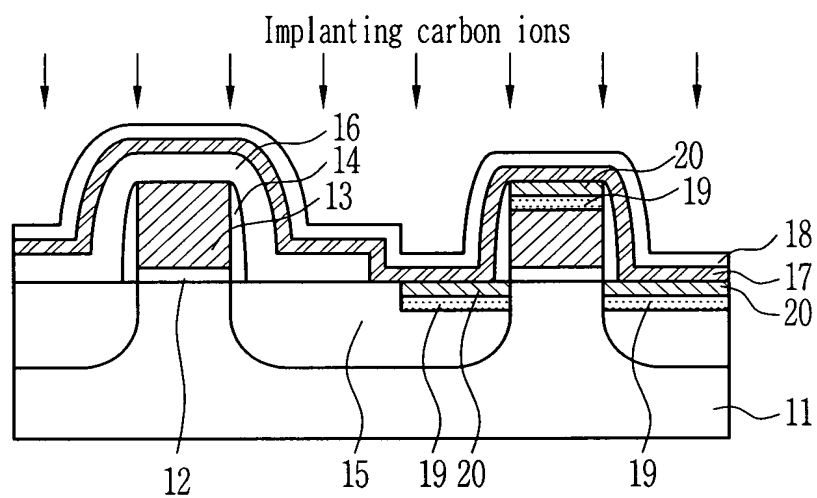


FIG. 1C



Implanting carbon ions



This cross-sectional view shows a semiconductor device with a central channel region 15 and two side regions 12 and 19. The channel region 15 is defined by a central gate stack 14 and 16, which is surrounded by a gate dielectric 13. The side regions 12 and 19 are defined by side gate stacks 21 and 19, which are surrounded by a side gate dielectric 19. The device is formed on a substrate 11.

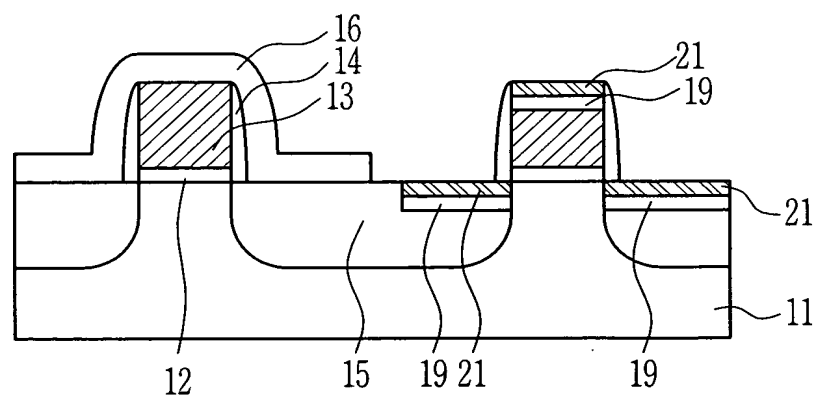


FIG. 2A

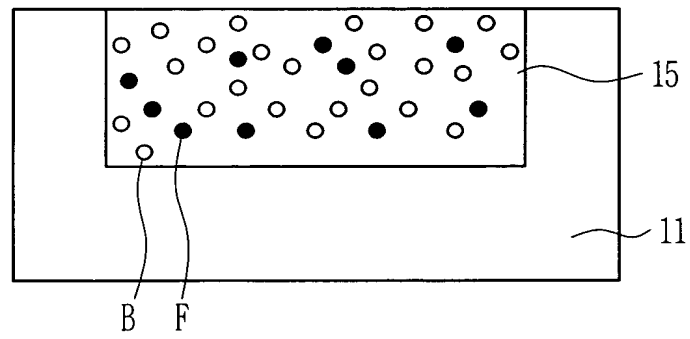


FIG. 2B

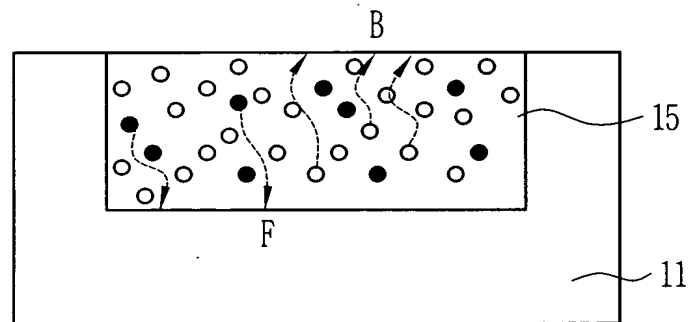


FIG. 2C

